4-Bit Magnitude Comparator

The MC14585B 4–Bit Magnitude Comparator is constructed with complementary MOS (CMOS) enhancement mode devices. The circuit has eight comparing inputs (A3, B3, A2, B2, A1, B1, A0, B0), three cascading inputs (A < B, A = B, and A > B), and three outputs (A < B, A = B, and A > B). This device compares two 4–bit words (A and B) and determines whether they are "less than", "equal to", or "greater than" by a high level on the appropriate output. For words greater than 4–bits, units can be cascaded by connecting outputs (A > B), (A < B), and (A = B) to the corresponding inputs of the next significant comparator. Inputs (A < B), (A = B), and (A > B) on the least significant (first) comparator are connected to a low, a high, and a low, respectively.

Applications include logic in CPU's, correction and/or detection of instrumentation conditions, comparator in testers, converters, and controls.

Features

- Diode Protection on All Inputs
- Expandable
- Applicable to Binary or 8421–BCD Code
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Capable of Driving Two Low-Power TTL Loads or One Low-Power Schottky TTL Load over the Rated Temperature Range
- Can be Cascaded See Figure 3
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable*
- This Device is Pb-Free and is RoHS Compliant

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

| Parameter | Symbol | Value | Unit |
|---|------------------------------------|----------------------------------|------|
| DC Supply Voltage Range | V_{DD} | -0.5 to +18.0 | V |
| Input or Output Voltage Range (DC or Transient) | V _{in} , V _{out} | -0.5 to V _{DD} + 0.5 | V |
| Input or Output Current (DC or Transient) per Pin | I _{in} , I _{out} | ±10 | mA |
| Power Dissipation per Package (Note 1) | P _D | 500 | mW |
| Ambient Temperature Range | T _A | -55 to +125 | °C |
| Storage Temperature Range | T _{stg} | -65 to +150 | °C |
| Lead Temperature (8–Second Soldering) | TL | 260 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Temperature Derating: "D/DW" Package: -7.0 mW/°C From 65° C To 125° C This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.



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SOIC-16 D SUFFIX CASE 751B

PIN ASSIGNMENT

| 1● | 16 | V _{DD} |
|----|----------------------------|--|
| 2 | 15 |] A3 |
| 3 | 14 |] B3 |
| 4 | 13 | (A u B) _{out} |
| 5 | 12 | (AtB) _{out} |
| 6 | 11 |] B0 |
| 7 | 10 |] A0 |
| 8 | 9 |] B1 |
| | 2 3 4 5 6 7 | 2 15 3 14 4 13 5 12 6 11 7 10 |

MARKING DIAGRAM



A = Assembly Location

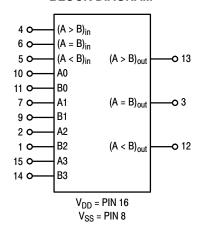
WL, L = Wafer Lot
 YY, Y = Year
 WW, W = Work Week
 G = Pb-Free Package

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|----------------|----------------------|-----------------------|
| MC14585BDG | SOIC-16 (Pb-Free) | 48 Units / Rail |
| MC14585BDR2G | SOIC-16 (Pb-Free) | 2500/Tape & Reel |
| NLV14585BDR2G* | SOIC-16 (Pb-Free) | 2500/Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BLOCK DIAGRAM



TRUTH TABLE (x = Don't Care)

| Inputs | | | | | | | | | |
|---------|---------|---------|---------|-------|---------|-------|-------|---------|-------|
| | Comp | aring | | С | ascadin | g | , | Outputs | |
| A3, B3 | A2, B2 | A1, B1 | A0, B0 | A < B | A = B | A > B | A < B | A = B | A > B |
| A3 > B3 | Х | Х | Х | Х | Х | Х | 0 | 0 | 1 |
| A3 = B3 | A2 > B2 | Х | х | х | х | х | 0 | 0 | 1 |
| A3 = B3 | A2 = B2 | A1 > B1 | х | х | х | х | 0 | 0 | 1 |
| A3 = B3 | A2 = B2 | A1 = B1 | A0 > B0 | x | х | х | 0 | 0 | 1 |
| A3 = B3 | A2 = B2 | A1 = B1 | A0 = B0 | 0 | 0 | Х | 0 | 0 | 1 |
| A3 = B3 | A2 = B2 | A1 = B1 | A0 = B0 | 0 | 1 | х | 0 | 1 | 0 |
| A3 = B3 | A2 = B2 | A1 = B1 | A0 = B0 | 1 | 0 | Х | 1 | 0 | 0 |
| A3 = B3 | A2 = B2 | A1 = B1 | A0 = B0 | 1 | 1 | х | 1 | 1 | 0 |
| A3 = B3 | A2 = B2 | A1 = B1 | A0 < B0 | Х | Х | Х | 1 | 0 | 0 |
| A3 = B3 | A2 = B2 | A1 < B1 | х | х | х | Х | 1 | 0 | 0 |
| A3 = B3 | A2 < B2 | х | х | x | х | х | 1 | 0 | 0 |
| A3 < B3 | Х | Х | Х | Х | Х | Х | 1 | 0 | 0 |

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

| | | | -55 | 5°C | | 25°C | | 125 | 5°C | |
|---|-----------------|------------------------|-------------------------------|----------------------|-------------------------------|---|----------------------|-------------------------------|----------------------|------|
| Characteristic | Symbol | V _{DD} Vdc | Min | Max | Min | Typ (Note 2) | Max | Min | Max | Unit |
| Output Voltage "0" Level V _{in} = V _{DD} or 0 | V _{OL} | 5.0 10 15 | - - - | 0.05 0.05 0.05 | - - - | 0 0 0 | 0.05 0.05 0.05 | - - - | 0.05 0.05 0.05 | Vdc |
| $V_{in} = 0 \text{ or } V_{DD}$ "1" Level | V _{OH} | 5.0 10 15 | 4.95 9.95 14.95 | - - - | 4.95 9.95 14.95 | 5.0 10 15 | - - - | 4.95 9.95 14.95 | - - - | Vdc |
| Input Voltage "0" Level (V _O = 4.5 or 0.5 Vdc) (V _O = 9.0 or 1.0 Vdc) (V _O = 13.5 or 1.5 Vdc) | V _{IL} | 5.0 10 15 | - - - | 1.5 3.0 4.0 | - - - | 2.25 4.50 6.75 | 1.5 3.0 4.0 | - - - | 1.5 3.0 4.0 | Vdc |
| "1" Level ($V_O = 0.5 \text{ or } 4.5 \text{ Vdc}$) ($V_O = 1.0 \text{ or } 9.0 \text{ Vdc}$) ($V_O = 1.5 \text{ or } 13.5 \text{ Vdc}$) | V _{IH} | 5.0 10 15 | 3.5 7.0 11 | - - - | 3.5 7.0 11 | 2.75 5.50 8.25 | - - - | 3.5 7.0 11 | - - - | Vdc |
| Output Drive Current (V _{OH} = 2.5 Vdc) Source (V _{OH} = 4.6 Vdc) (V _{OH} = 9.5 Vdc) (V _{OH} = 13.5 Vdc) | I _{OH} | 5.0 5.0 10 15 | -3.0 -0.64 -1.6 -4.2 | - - - - | -2.4 -0.51 -1.3 -3.4 | -4.2 -0.88 -2.25 -8.8 | - - - - | -1.7 -0.36 -0.9 -2.4 | - - - - | mAdc |
| $(V_{OL} = 0.4 \text{ Vdc})$ Sink $(V_{OL} = 0.5 \text{ Vdc})$ $(V_{OL} = 1.5 \text{ Vdc})$ | I _{OL} | 5.0 10 15 | 0.64 1.6 4.2 | - - - | 0.51 1.3 3.4 | 0.88 2.25 8.8 | - - - | 0.36 0.9 2.4 | - - - | mAdc |
| Input Current | I _{in} | 15 | - | ±0.1 | - | ±0.00001 | ±0.1 | - | ±1.0 | μAdc |
| Input Capacitance (V _{in} = 0) | C _{in} | ı | _ | _ | - | 5.0 | 7.5 | _ | - | pF |
| Quiescent Current (Per Package) | I _{DD} | 5.0 10 15 | - - - | 5.0 10 20 | - - - | 0.005 0.010 0.015 | 5.0 10 20 | - - - | 150 300 600 | μAdc |
| Total Supply Current (Notes 3, 4) (Dynamic plus Quiescent, Per Package) (C _L = 50 pF on all outputs, all buffers switching) | I _T | 5.0 10 15 | | | $I_T = ('$ | 0.6 μΑ/kHz) f 1.2 μΑ/kHz) f 1.8 μΑ/kHz) f | + I _{DD} | | | μAdc |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

3. The formulas given are for the typical characteristics only at 25°C.

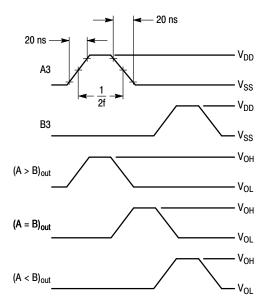
4. To calculate total supply current aloads other than 50 pF: I_T(C_L) = I_T(50 pF) + (C_L – 50) Vfk where: I_T is in μA (per package), C_L in pF,

- $V = (V_{DD} V_{SS})$ in volts, f in kHz is input frequency, and k = 0.001.

SWITCHING CHARACTERISTICS (Note 5) ($C_L = 50 \text{ pF}, T_A = 25^{\circ}\text{C}$)

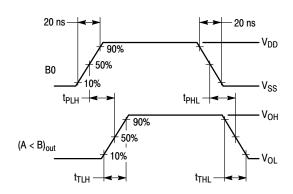
| Characteristic | Symbol | V _{DD} | Min | Typ (Note 6) | Max | Unit |
|---|--|-----------------|-------------|-------------------|-------------------|------|
| Output Rise and Fall Time $t_{TLH}, t_{THL} = (1.5 \text{ ns/pF}) C_L + 25 \text{ ns}$ $t_{TLH}, t_{THL} = (0.75 \text{ ns/pF}) C_L + 12.5 \text{ ns}$ $t_{TLH}, t_{THL} = (0.55 \text{ ns/pF}) C_L + 9.5 \text{ ns}$ | t _{TLH} , t _{THL} | 5.0 10 15 | - - - | 100 50 40 | 200 100 80 | ns |
| Turn–On, Turn–Off Delay Time t_{PLH} , t_{PHL} = (1.7 ns/pF) C_L + 345 ns t_{PLH} , t_{PHL} = (0.66 ns/pF) C_L + 147 ns t_{PLH} , t_{PHL} = (0.5 ns/pF) C_L + 105 ns | t _{PLH} , t _{PHL} | 5.0 10 15 | - - - | 430 180 130 | 860 360 260 | ns |

- 5. The formulas given are for the typical characteristics only at 25°C.
- 6. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.



Inputs (A>B) and (A=B) high, and inputs B2, A2, B1, A1, B0, A0 and (A<B) low.
f in respect to a system clock.

Figure 1. Dynamic Power Dissipation Signal Waveforms



Inputs (A>B) and (A=B) high, and inputs B3, A3, B2, A2, B1, A1, A0, and (A<B) low.

Figure 2. Dynamic Signal Waveforms

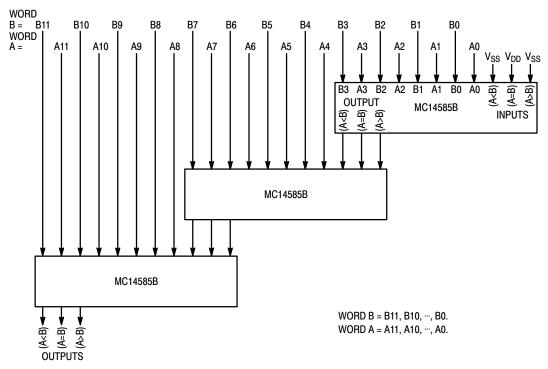
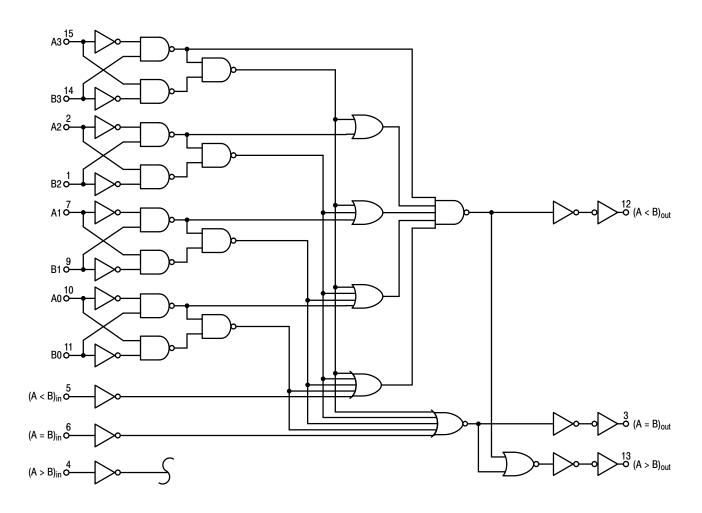


Figure 3. Cascading Comparators

LOGIC DIAGRAM





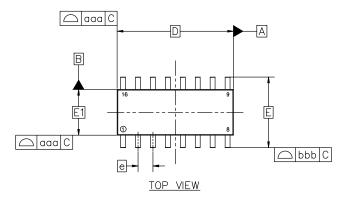


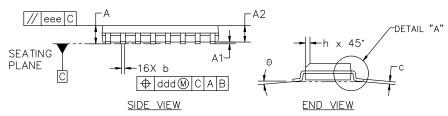
SOIC-16 9.90x3.90x1.50 1.27P CASE 751B ISSUE L

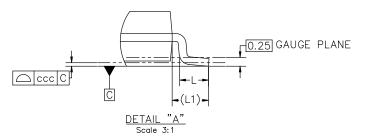
DATE 29 MAY 2024

NOTES:

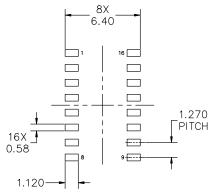
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
- 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15mm PER SIDE.
- 5. DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127mm TOTAL IN EXCESS OF THE 6 DIMENSION AT MAXIMUM MATERIAL CONDITION.







| MILLIMETERS | | | | | | | |
|-------------|----------|----------|----------|--|--|--|--|
| DIM | MIN | NOM | MAX | | | | |
| А | 1.35 | 1.55 | 1.75 | | | | |
| A1 | 0.00 | 0.05 | 0.10 | | | | |
| A2 | 1.35 | 1.50 | 1.65 | | | | |
| b | 0.35 | 0.42 | 0.49 | | | | |
| С | 0.19 | 0.22 | 0.25 | | | | |
| D | | 9.90 BSC | | | | | |
| Е | 6.00 BSC | | | | | | |
| E1 | 3.90 BSC | | | | | | |
| е | 1.27 BSC | | | | | | |
| h | 0.25 | | 0.50 | | | | |
| L | 0.40 | 0.83 | 1.25 | | | | |
| L1 | | 1.05 REF | | | | | |
| Θ | 0. | | 7° | | | | |
| TOLERAN | CE OF FO | ORM AND | POSITION | | | | |
| aaa | 0.10 | | | | | | |
| bbb | 0.20 | | | | | | |
| ссс | | 0.10 | | | | | |
| ddd | | 0.25 | · · · | | | | |
| eee | | 0.10 | | | | | |



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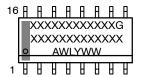
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SOIC-16 9.90x3.90x1.50 1.27P

CASE 751B ISSUE L

DATE 29 MAY 2024

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code A = Assembly Location

WL = Wafer Lot
 Y = Year
 WW = Work Week
 G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

| STYLE 1: | | STYLE 2: | | STYLE 3: | S | TYLE 4: | |
|---|--|---|---|---|---|---------|-------------------|
| | COLLECTOR | PIN 1. | CATHODE | PIN 1. | COLLECTOR, DYE #1 | PIN 1. | COLLECTOR, DYE #1 |
| | BASE | 2. | ANODE | 2. | BASE. #1 | 2. | |
| 3. | EMITTER | 3. | NO CONNECTION | 3. | EMITTER. #1 | 3. | |
| 4. | NO CONNECTION | 4. | CATHODE | 4. | COLLECTOR, #1 | 4. | COLLECTOR, #2 |
| 5. | EMITTER | 5. | CATHODE | 5. | COLLECTOR, #2 | 5. | COLLECTOR, #3 |
| 6. | BASE | 6. | NO CONNECTION | 6. | BASE, #2 | 6. | COLLECTOR, #3 |
| 7. | COLLECTOR | 7. | ANODE | 7. | EMITTER, #2 | 7. | COLLECTOR, #4 |
| 8. | COLLECTOR | 8. | CATHODE | 8. | COLLECTOR, #2 | 8. | COLLECTOR, #4 |
| 9. | BASE | 9. | CATHODE | 9. | COLLECTOR, #3 | 9. | BASE, #4 |
| 10. | EMITTER | 10. | ANODE | 10. | BASE, #3 | 10. | EMITTER, #4 |
| 11. | NO CONNECTION | 11. | NO CONNECTION | 11. | EMITTER, #3 | 11. | |
| | EMITTER | 12. | CATHODE | 12. | COLLECTOR, #3 | 12. | |
| 13. | BASE | 13. | | 13. | COLLECTOR, #4 | 13. | BASE, #2 |
| 14. | COLLECTOR | 14. | NO CONNECTION | 14. | BASE, #4 | 14. | |
| 15. | EMITTER | 15. | ANODE | 15. | EMITTER, #4 | 15. | |
| 16. | COLLECTOR | 16. | CATHODE | 16. | COLLECTOR, #4 | 16. | EMITTER, #1 |
| | | | | | | | |
| STYLE 5: | | STYLE 6: | | STYLE 7: | | | |
| PIN 1. | DRAIN, DYE #1 | PIN 1. | CATHODE | PIN 1. | SOURCE N-CH | | |
| 2. | DRAIN, #1 | 2. | CATHODE | 2. | COMMON DRAIN (OUTPUT) | | |
| 3. | DRAIN. #2 | 3. | CATHODE | 3. | COMMON DRAIN (OUTPUT) | | |
| | שוויאווי, דב | ٥. | | ٥. | | | |
| 4. | | 3. 4. | CATHODE | 3. 4. | | | |
| 4. 5. | DRAIN, #2 DRAIN, #3 | | CATHODE CATHODE | | GATE P-CH COMMON DRAIN (OUTPUT) | | |
| 5. 6. | DRAIN, #2 DRAIN, #3 DRAIN, #3 | 4. 5. 6. | CATHODE CATHODE CATHODE | 4. 5. 6. | GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) | | |
| 5. | DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 | 4. 5. 6. 7. | CATHODE CATHODE CATHODE CATHODE | 4. 5. 6. 7. | GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) | | |
| 5. 6. 7. 8. | DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 | 4. 5. 6. 7. | CATHODE CATHODE CATHODE CATHODE CATHODE | 4. 5. 6. 7. 8. | GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH | | |
| 5. 6. 7. 8. | DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 | 4. 5. 6. 7. 8. | CATHODE CATHODE CATHODE CATHODE CATHODE ANODE | 4. 5. 6. 7. 8. 9. | GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH | | |
| 5. 6. 7. 8. 9. | DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 | 4. 5. 6. 7. 8. 9. | CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE | 4. 5. 6. 7. 8. 9. | GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) | | |
| 5. 6. 7. 8. 9. 10. | DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 | 4. 5. 6. 7. 8. 9. 10. | CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE | 4. 5. 6. 7. 8. 9. 10. | GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) | | |
| 5. 6. 7. 8. 9. 10. 11. | DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 | 4. 5. 6. 7. 8. 9. 10. 11. | CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE ANODE ANODE | 4. 5. 6. 7. 8. 9. 10. 11. | GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) | | |
| 5. 6. 7. 8. 9. 10. 11. 12. | DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2 | 4. 5. 6. 7. 8. 9. 10. 11. 12. | CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE | 4. 5. 6. 7. 8. 9. 10. 11. 12. | GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURGE P-CH SOURGE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE N-CH | | |
| 5. 6. 7. 8. 9. 10. 11. 12. 13. | DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 GATE, #4 GATE, #3 SOURCE, #3 GOURCE, #3 GOURCE, #2 SOURCE, #2 | 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. | CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE | 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. | GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) CATE N-CH COMMON DRAIN (OUTPUT) | | |
| 5. 6. 7. 8. 9. 10. 11. 12. 13. 14. | DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2 SOURCE, #2 GATE, #1 | 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14. | CATHODE CATHODE CATHODE CATHODE CATHODE ANODE | 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14. | GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE N-CH COMMON DRAIN (OUTPUT) GATE N-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) | | |
| 5. 6. 7. 8. 9. 10. 11. 12. 13. | DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 GATE, #4 GATE, #3 SOURCE, #3 GOURCE, #3 GOURCE, #2 SOURCE, #2 | 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. | CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE | 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. | GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) CATE N-CH COMMON DRAIN (OUTPUT) | | |

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